

NTMFS4C028N

MOSFET – Power, Single, N-Channel, SO-8 FL 30 V, 52 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- CPU Power Delivery
- DC-DC Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	16.4	A
		$T_A = 80^{\circ}\text{C}$		12.3	
Power Dissipation $R_{\theta JA}$ (Note 1)		$T_A = 25^{\circ}\text{C}$	P_D	2.51	W
Continuous Drain Current $R_{\theta JA} \leq 10\text{ s}$ (Note 1)		$T_A = 25^{\circ}\text{C}$	I_D	25.3	A
		$T_A = 80^{\circ}\text{C}$		19.0	
Power Dissipation $R_{\theta JA} \leq 10\text{ s}$ (Note 1)		$T_A = 25^{\circ}\text{C}$	P_D	6.0	W
Continuous Drain Current $R_{\theta JA}$ (Note 2)		$T_A = 25^{\circ}\text{C}$	I_D	9.0	A
		$T_A = 80^{\circ}\text{C}$		6.8	
Power Dissipation $R_{\theta JA}$ (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	0.76	W
Continuous Drain Current $R_{\theta JC}$ (Note 1)		$T_C = 25^{\circ}\text{C}$	I_D	52	A
		$T_C = 80^{\circ}\text{C}$		39	
Power Dissipation $R_{\theta JC}$ (Note 1)		$T_C = 25^{\circ}\text{C}$	P_D	25.5	W
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$		I_{DM}	146	A
Current Limited by Package		$T_A = 25^{\circ}\text{C}$	I_{Dmax}	80	A
Operating Junction and Storage Temperature			T_J , T_{STG}	-55 to +150	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	23	A
Drain to Source dV/dt			dV/d_t	7.0	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}\text{C}$, $V_{GS} = 10\text{ V}$, $I_L = 29\text{ A}_{pk}$, $L = 0.1\text{ mH}$, $R_{GS} = 25\text{ }\Omega$) (Note 3)			E_{AS}	42	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

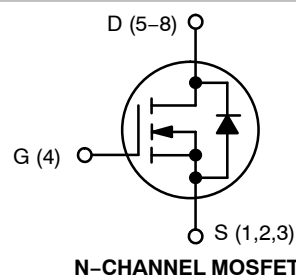
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



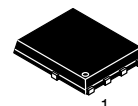
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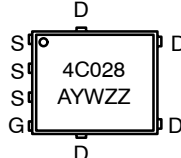
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	4.73 m Ω @ 10 V	52 A
	7.0 m Ω @ 4.5 V	



MARKING DIAGRAMS



SO-8 FLAT LEAD
CASE 488AA
STYLE 1



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4C028NT1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NTMFS4C028NT3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.
3. Parts are 100% tested at $T_J = 25^\circ\text{C}$, $V_{GS} = 10\text{ V}$, $I_L = 20\text{ A}_{pk}$, $EAS = 20\text{ mJ}$.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	4.9	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	49.8	
Junction-to-Ambient – Steady State (Note 5)	$R_{\theta JA}$	164.6	
Junction-to-Ambient – ($t \leq 10\text{ s}$) (Note 4)	$R_{\theta JA}$	21.0	

4. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
5. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage (transient)	$V_{(BR)DSS(t)}$	$V_{GS} = 0\text{ V}$, $I_{D(aval)} = 8.4\text{ A}$, $T_{case} = 25^\circ\text{C}$, $t_{transient} = 100\text{ ns}$	34			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			14.4		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$, $V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		1.0 10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 6)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	1.3		2.1	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.8		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 18\text{ A}$		3.9 5.8	4.73 7.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}$, $I_D = 15\text{ A}$		50		S
Gate Resistance	R_G	$T_A = 25^\circ\text{C}$	0.3	1.0	2.0	Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$, $V_{DS} = 15\text{ V}$		1252		pF
Output Capacitance	C_{OSS}			610		
Reverse Transfer Capacitance	C_{RSS}			126		
Capacitance Ratio	C_{RSS}/C_{ISS}	$V_{GS} = 0\text{ V}$, $V_{DS} = 15\text{ V}$, $f = 1\text{ MHz}$		0.101		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}$, $V_{DS} = 15\text{ V}$; $I_D = 30\text{ A}$		10.9		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.9		
Gate-to-Source Charge	Q_{GS}			3.4		
Gate-to-Drain Charge	Q_{GD}			5.4		
Gate Plateau Voltage	V_{GP}			3.1		V
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 15\text{ V}$; $I_D = 30\text{ A}$		22.2		nC

SWITCHING CHARACTERISTICS (Note 7)

6. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
7. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS (Note 7)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		10		ns
Rise Time	t_r			32		
Turn-Off Delay Time	$t_{d(OFF)}$			16		
Fall Time	t_f			6.0		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		7.0		ns
Rise Time	t_r			28		
Turn-Off Delay Time	$t_{d(OFF)}$			20		
Fall Time	t_f			4.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.79	1.1	V
			T _J = 125°C		0.65		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A			31		ns
Charge Time	t _a				15		
Discharge Time	t _b				16		
Reverse Recovery Charge	Q _{RR}				15		nC

6. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

7. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

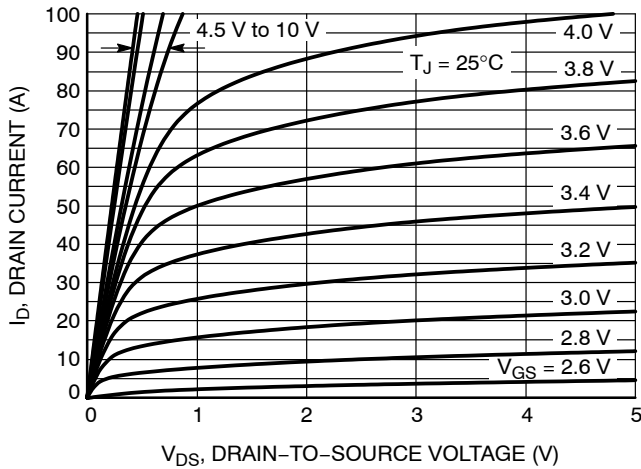


Figure 1. On-Region Characteristics

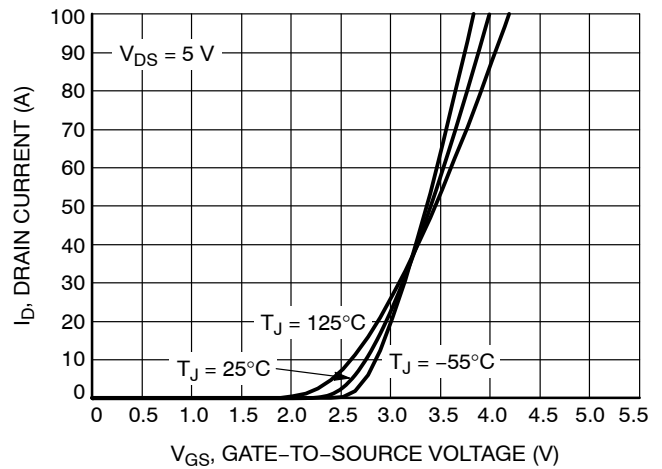


Figure 2. Transfer Characteristics

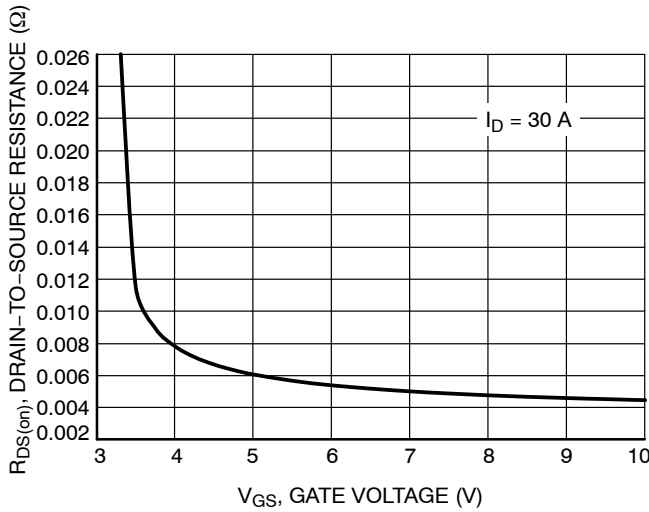


Figure 3. On-Resistance vs. Gate-to-Source Voltage

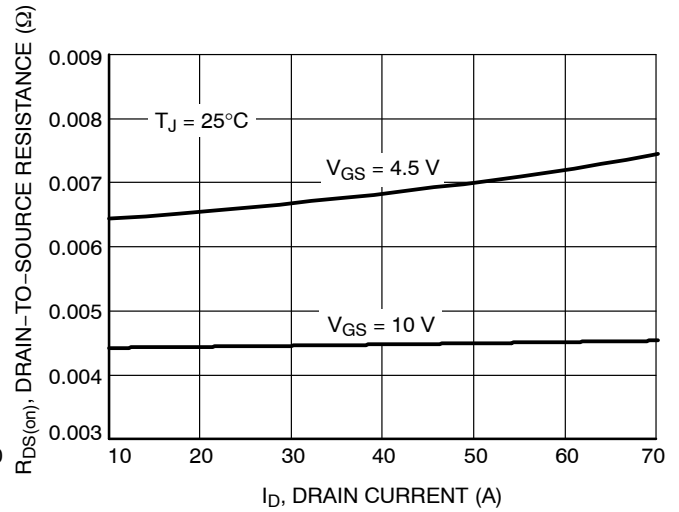


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

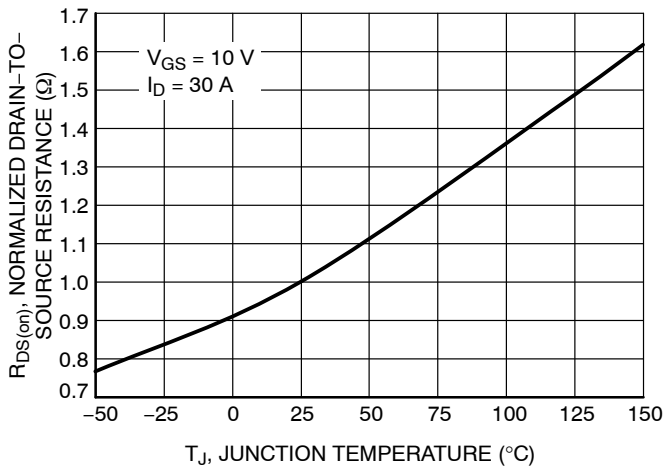


Figure 5. On-Resistance Variation with Temperature

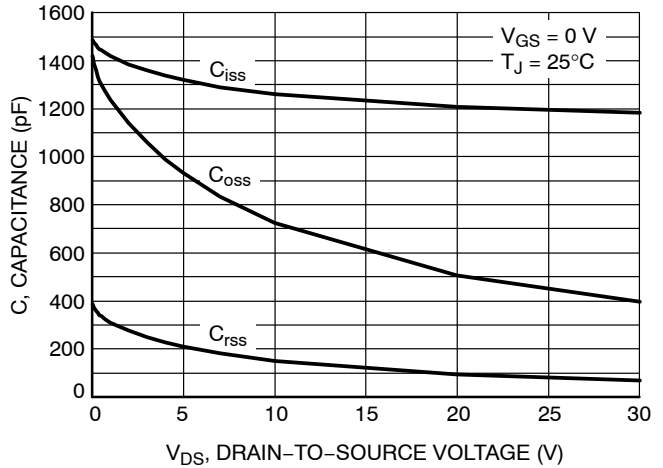


Figure 6. Capacitance Variation

TYPICAL CHARACTERISTICS

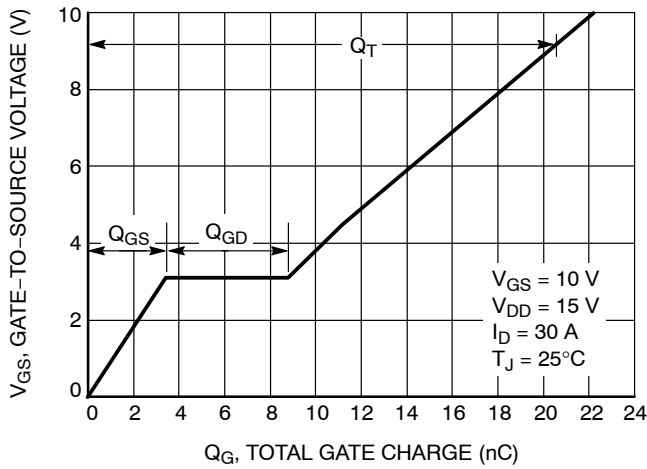


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

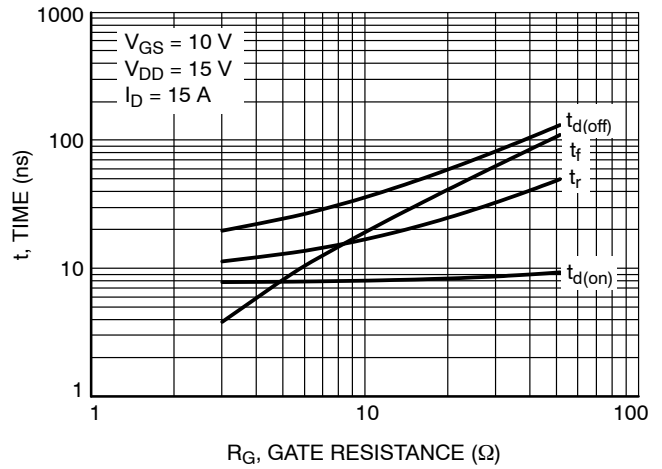


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

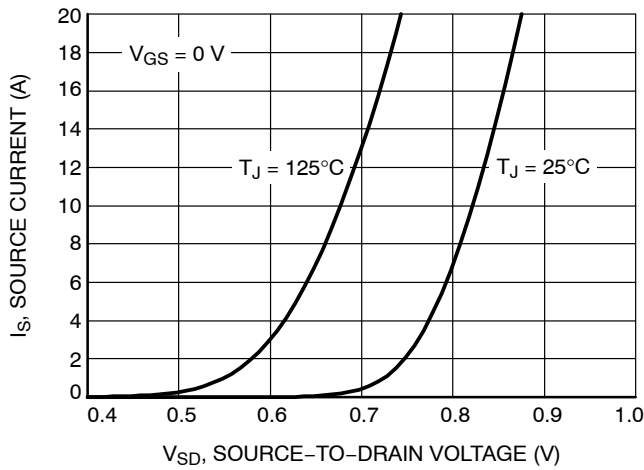


Figure 9. Diode Forward Voltage vs. Current

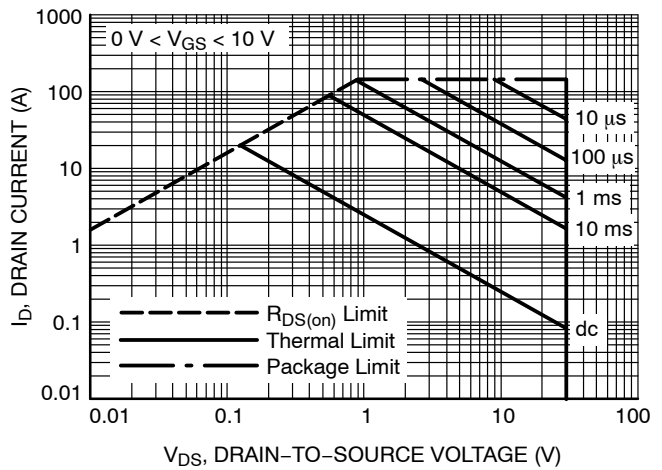


Figure 10. Maximum Rated Forward Biased Safe Operating Area

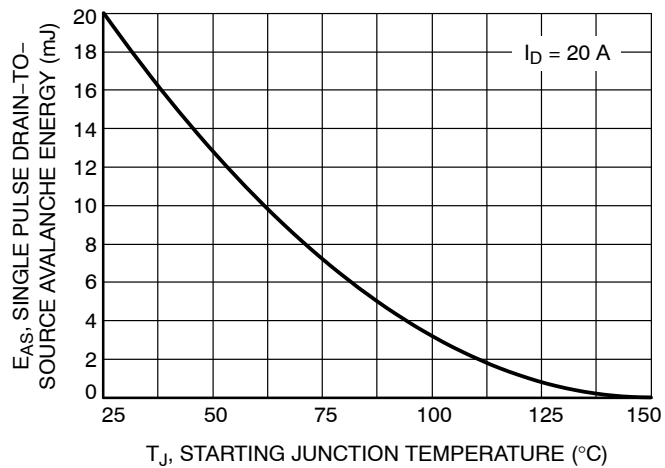


Figure 11. Maximum Avalanche Energy vs. Starting Junction Temperature

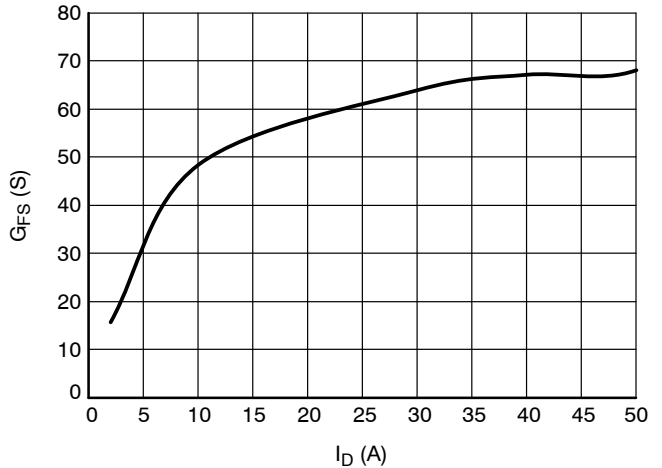


Figure 12. G_{FS} vs. I_D

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TYPICAL CHARACTERISTICS

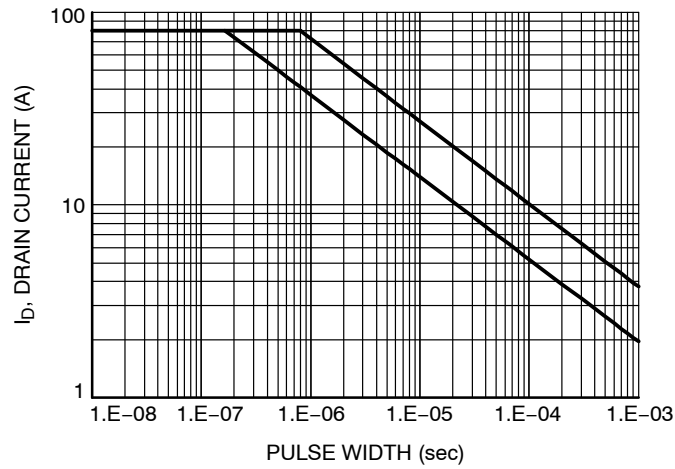


Figure 13. Avalanche Characteristics

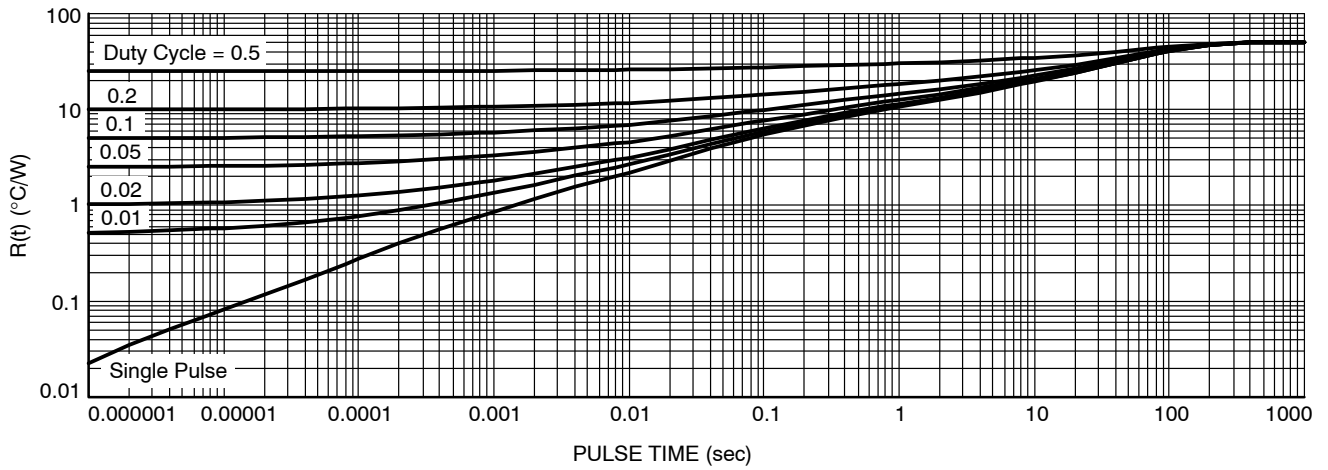


Figure 14. Thermal Response

